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[Vishay/Siliconix](#)
[SI4100DY-T1-E3](#)

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Si4100DY
 Vishay Siliconix

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^d	Q _g (Typ.)
100	0.063 at V _{GS} = 10 V	6.8	9 nC
	0.084 at V _{GS} = 6 V	5.8	

FEATURES

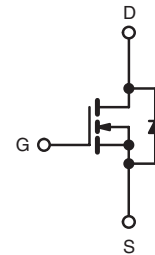
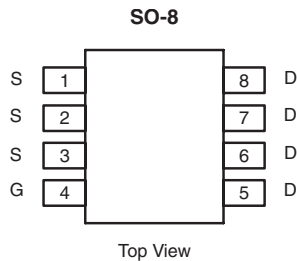
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- 100 % UIS Tested



RoHS
 COMPLIANT
 HALOGEN
FREE
 Available

APPLICATIONS

- High Frequency Boost Converter
- LED Backlight for LCD TV



N-Channel MOSFET

Ordering Information: Si4100DY-T1-E3 (Lead (Pb)-free)
 Si4100DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	6.8
		T _C = 70 °C	5.4
		T _A = 25 °C	4.4 ^{a, b}
		T _A = 70 °C	3.5 ^{a, b}
Pulsed Drain Current	I _{DM}	20	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	2.1 ^{a, b}
Single Avalanche Current	I _{AS}	19	mJ
Single Avalanche Energy	E _{AS}	18	
Maximum Power Dissipation	P _D	T _C = 25 °C	6
		T _C = 70 °C	3.8
		T _A = 25 °C	2.5 ^{a, b}
		T _A = 70 °C	1.6 ^{a, b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, c}	R _{thJA}	37	50	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	17	21	

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 85 °C/W.
- T_C = 25 °C.

Si4100DY

Vishay Siliconix



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		120		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-9		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.4\text{ A}$		0.051	0.063	Ω
		$V_{GS} = 6\text{ V}, I_D = 3.8\text{ A}$		0.069	0.084	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 4.4\text{ A}$		10		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		600		pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			50		
Total Gate Charge	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.4\text{ A}$		13.5	20	nC
		$V_{DS} = 50\text{ V}, V_{GS} = 6\text{ V}, I_D = 4.4\text{ A}$		9	13.5	
Q_{gs}			3			
Q_{gd}			4.6			
Gate Resistance	R_g	$f = 1\text{ MHz}$		1		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 14.3\text{ }\Omega$ $I_D \cong 3.5\text{ A}, V_{GEN} = 6\text{ V}, R_g = 1\text{ }\Omega$		15	25	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			12	20	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 14.3\text{ }\Omega$ $I_D \cong 3.5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		10	15	
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			15	25	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			5	A
Pulse Diode Forward Current	I_{SM}				20	
Body Diode Voltage	V_{SD}	$I_S = 3.5\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 3.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		45	70	ns
Body Diode Reverse Recovery Charge	Q_{rr}			80	120	nC
Reverse Recovery Fall Time	t_a			33		ns
Reverse Recovery Rise Time	t_b			12		

Notes:

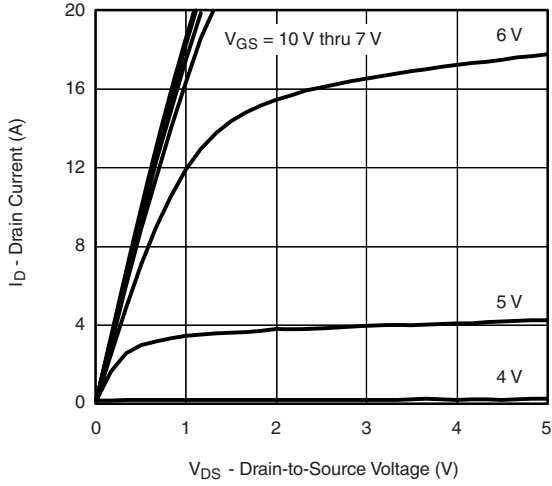
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

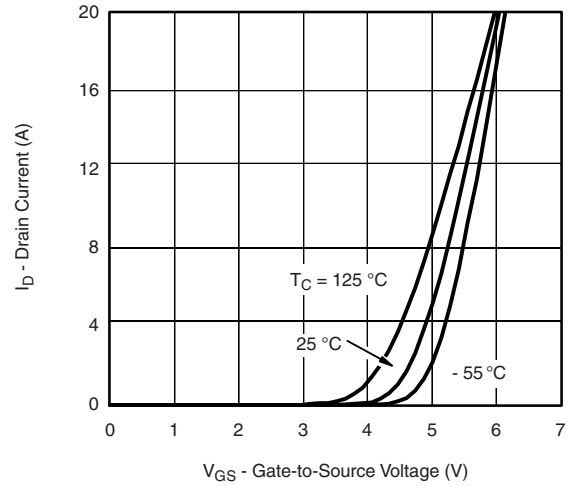


Si4100DY
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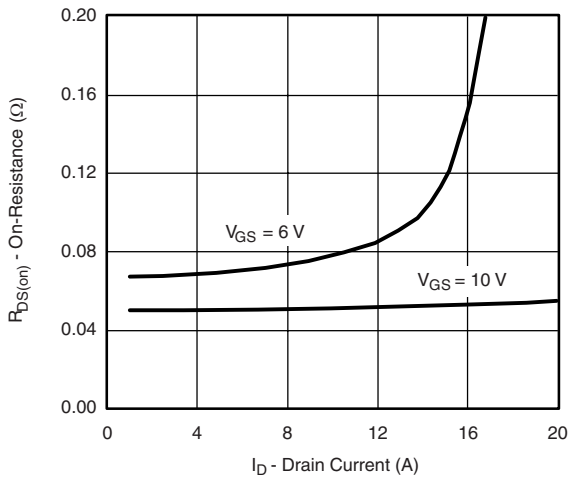
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



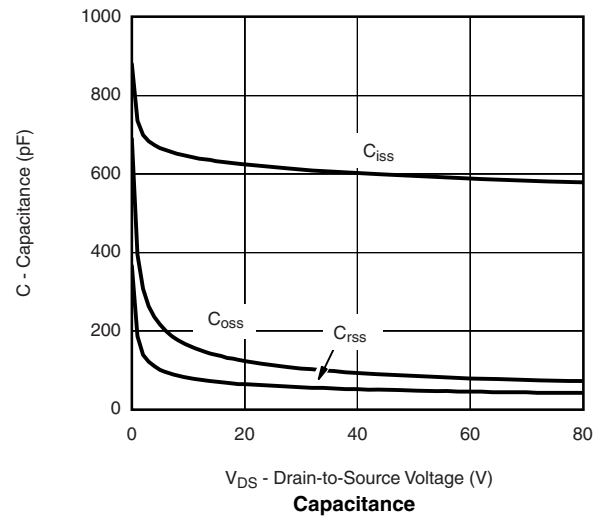
Output Characteristics



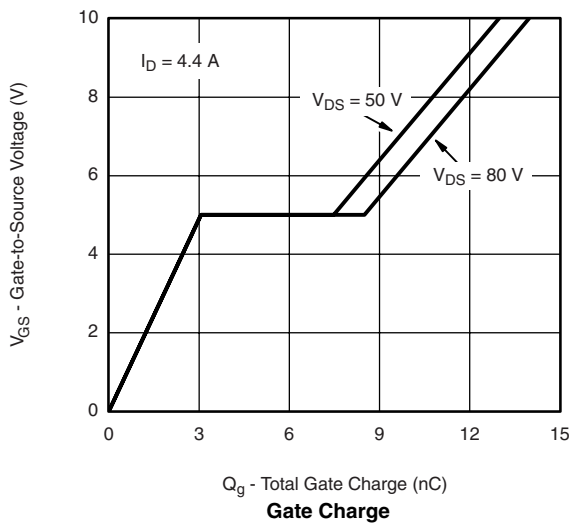
Transfer Characteristics



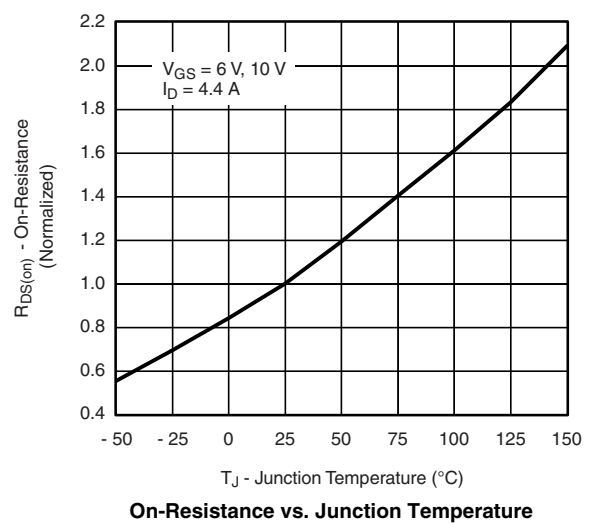
On-Resistance vs. Drain Current



Capacitance



Gate Charge



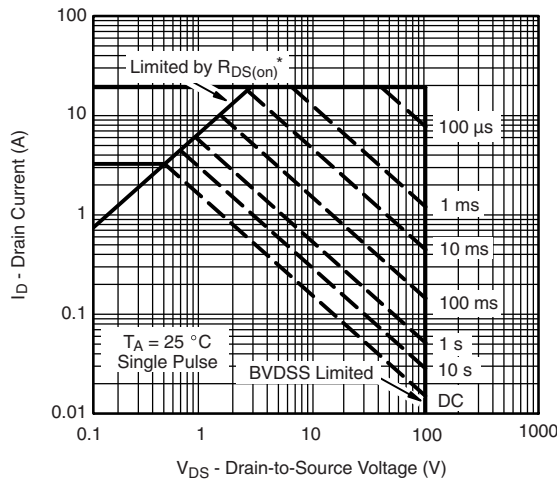
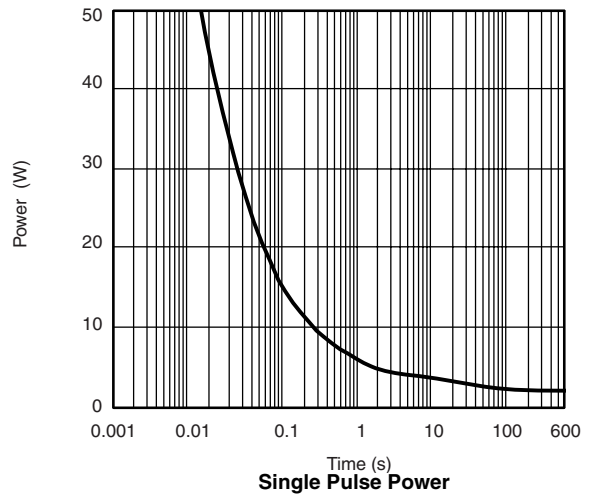
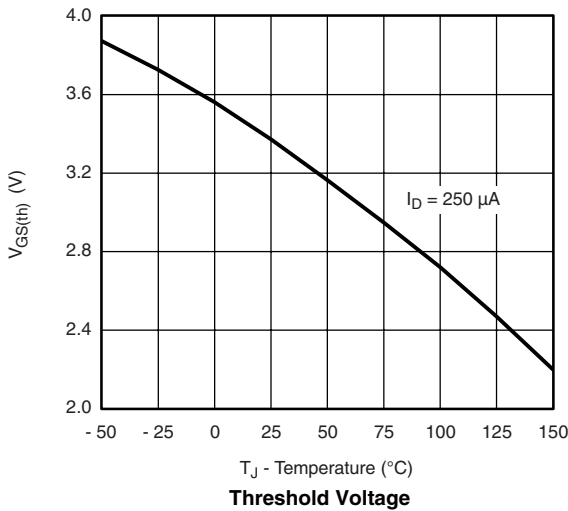
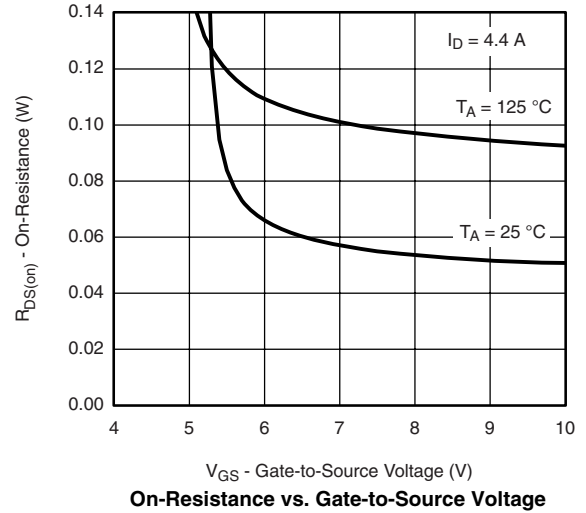
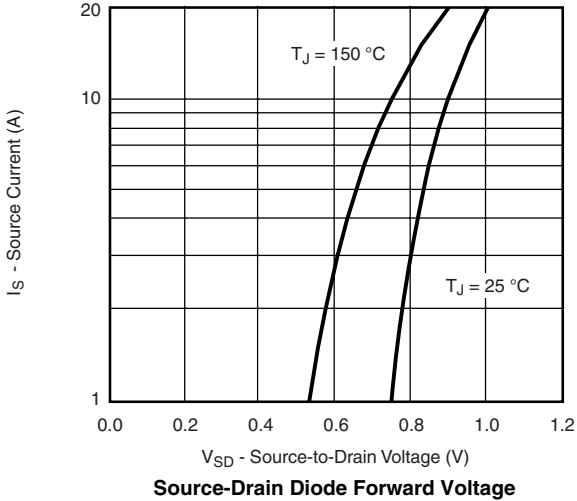
On-Resistance vs. Junction Temperature

Si4100DY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

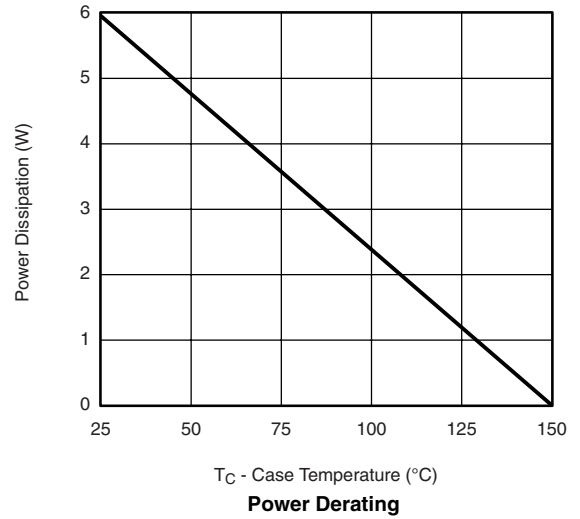
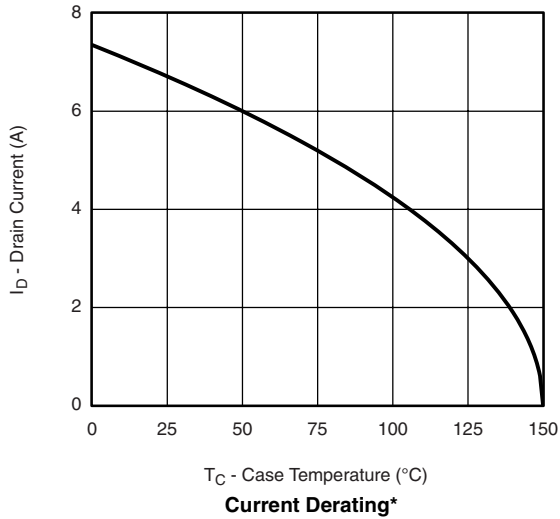


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



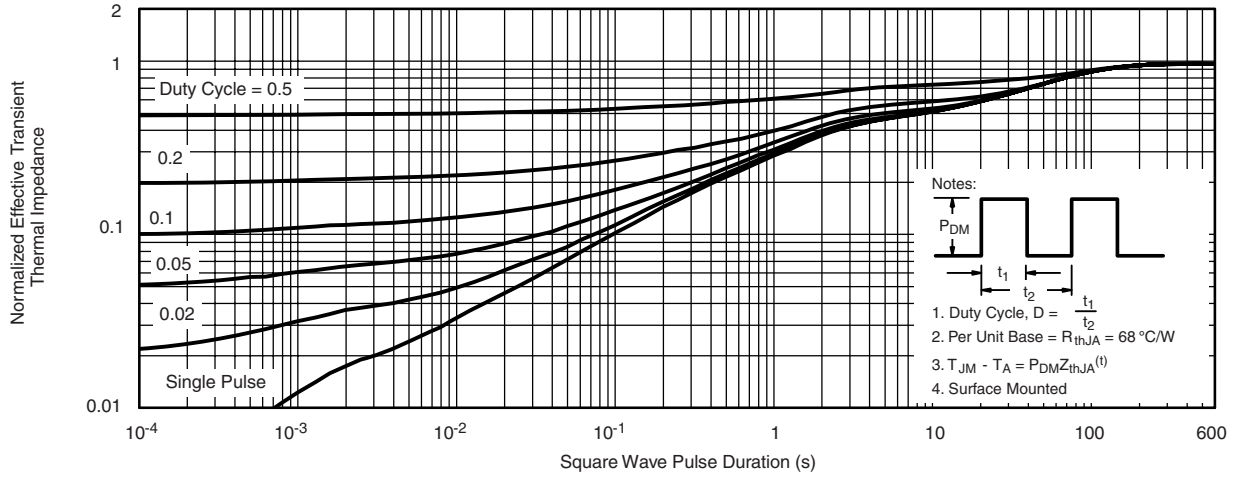
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si4100DY

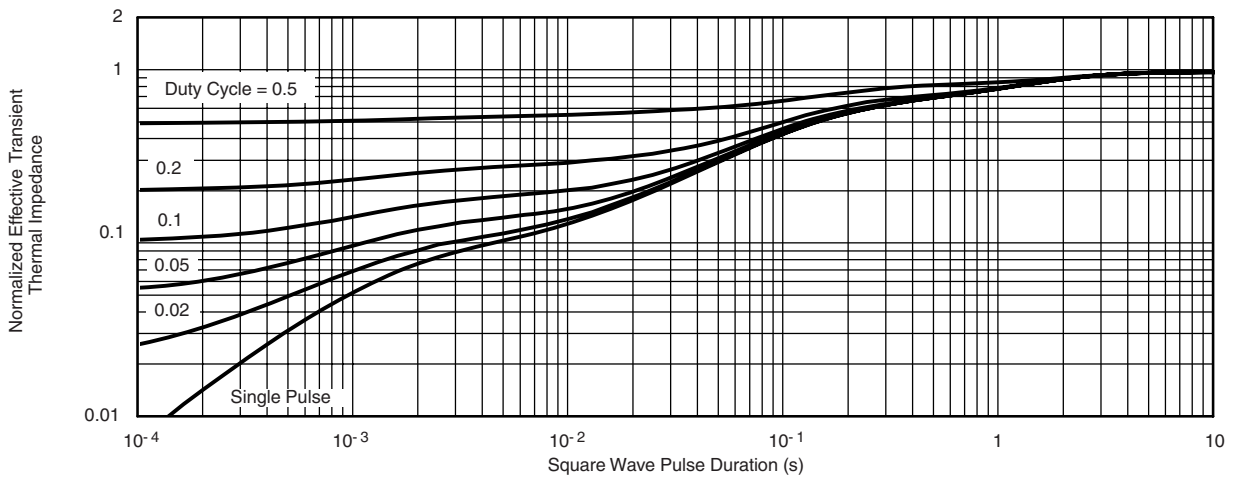
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69251.

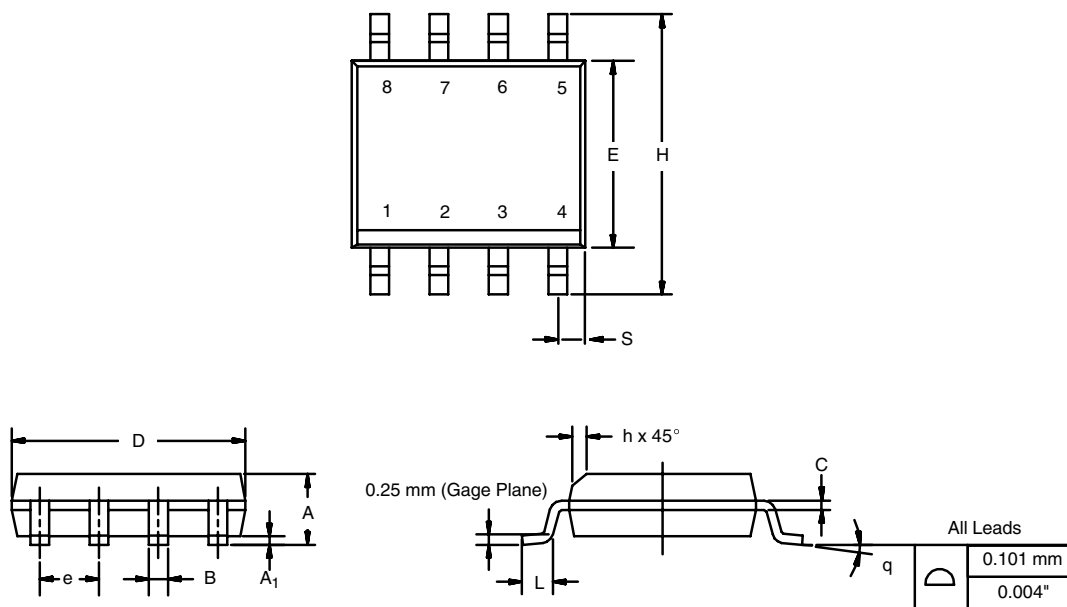


Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026

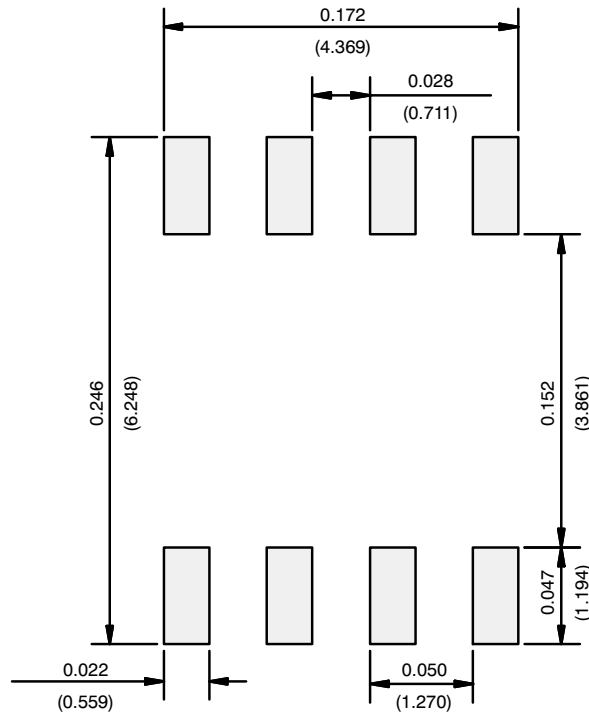
ECN: C-06527-Rev. I, 11-Sep-06
DWG: 5498

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
 Dimensions in Inches/(mm)

[Return to Index](#)

APPLICATION NOTE



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